

AMENDMENTS TO THE CLAIMS

Claim 1 (Original): A method of forming a photo sensor in a photo diode formed on a semiconductor wafer, a surface
5 of the semiconductor comprising a substrate with first-type dopants, and an insulating layer positioned on a surface of the substrate and surrounding the photo sensor, the method comprising:

performing a first ion implantation process utilizing
10 second-type dopants to form a plurality of first doped regions on a surface of the photo sensor; and

a1 performing a second ion implantation process utilizing second-type dopants to form a second doped region on the surface of the photo sensor, and the second
15 doped region being overlapped with a partial region of each of the first doped regions.

Claim 2 (original): The method of claim 1 wherein the dopants in the first doped regions and in the second doped
20 region interact with neighboring substrate to form a plurality of depletion regions.

Claim 3 (original): The method of claim 1 wherein the first-type dopants are N-type, and the second-type
25 dopants are P-type.

Claim 4 (original): The method of claim 1 wherein the first-type dopants are P-type, and the second-type
30 dopants are N-type.

Claim 5 (original): The method of claim 1 wherein the substrate further comprises an epitaxial silicon layer, and each of the first doped regions and the second doped region are formed inside the epitaxial silicon layer.

Claim 6 (original): The method of claim 1 wherein a dopant density of the first ion implantation process is less than a dopant density of the second ion implantation process.

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Claim 7 (original): The method of claim 1 wherein the surface of the semiconductor wafer further comprises a logic circuit region, and the second ion implantation process forms at least a lightly doped drain (LDD) within the logic circuit region.

Claim 8 (original): The method of claim 1 wherein the method further comprises an annealing process for driving-in the dopants in the second doped region.

Claim 9 (original): The method of claim 1 wherein each of the depletion regions formed between the neighboring first doped regions is a complete depletion region, and a capacitance of each of the depletion regions is approximately equal to zero for increasing a sensing area, decreasing dark current, and further increasing photo current and photon conversion gain.

Claim 10 (original): The method of claim 1 wherein the second doped region is utilized to be a conducting wire

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of the photo sensor.

Claims 11-19 (Canceled)
